mosaic

Mosaic Semiconductor Inc.

512 K X 8 SRAM

MS8512FK-25/30/35

Issue 1.0 : June 1992

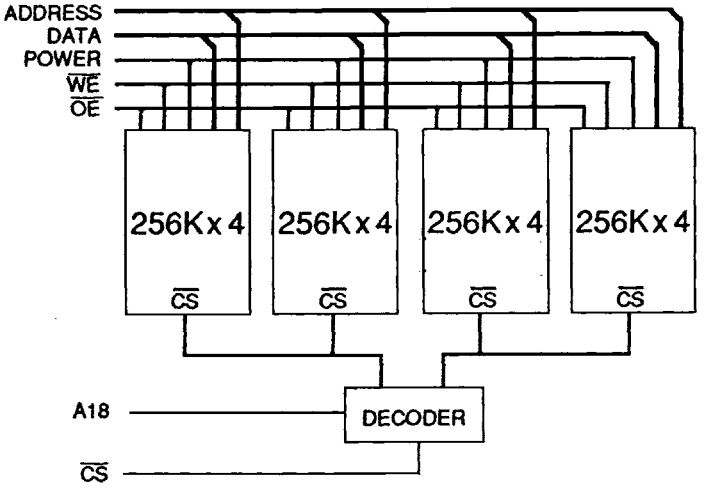
ADVANCE PRODUCT INFORMATION

524,288 x 8 CMOS High Speed Static RAM

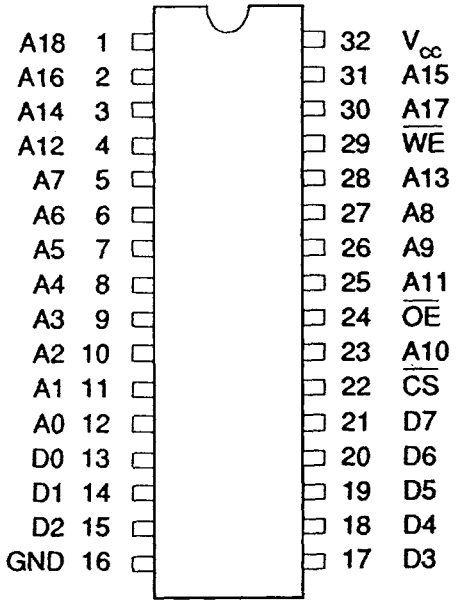
Features

Very Fast Access Times of 25/30/35 ns
JEDEC Standard 32 pin DIL footprint
Operating Power 2005 mW (max.)
Low Power Standby 888 mW (max.)
10 mW (max.) - L Version
Battery back-up capability
Completely Static Operation
Common data inputs & outputs
Onboard Decoupling Capacitors

Block Diagram



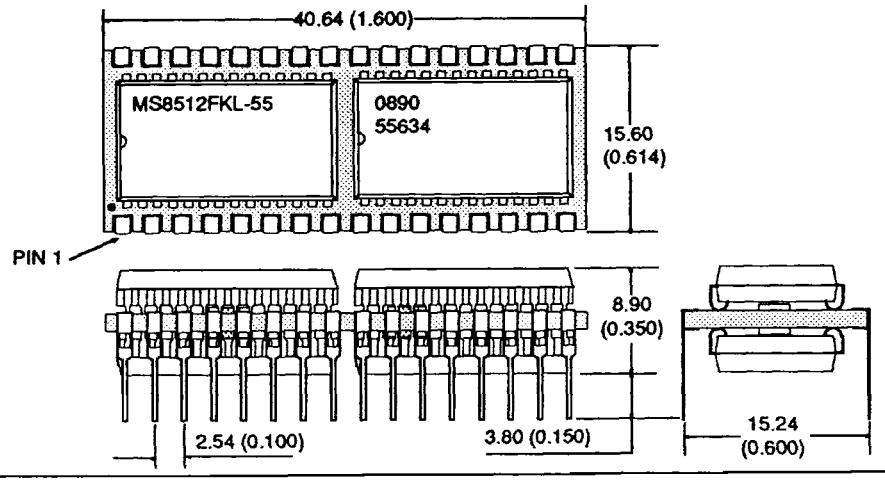
Pin Definition



Pin Functions

A0-A18	Address Inputs
D0-7	Data Input/Output
$\overline{CS}$	Chip Select
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
V_{CC}	Power (+5V)
GND	Ground

Package Details Dimensions in mm (inches).



MOSCS068

Absolute Maximum Ratings (1)

Voltage on any pin relative to V_{SS} (2)	V_T	-0.5V to +7	V
Power Dissipation	P_T	1	W
Storage Temperature	T_{STG}	-55 to +150	°C

Notes : (1) Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

(2) V_t can be -2.0V pulse of less than 10ns.

Recommended Operating Conditions

		min	typ	max	
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Input High Voltage	V_{IH}	2.2	-	6.0	V
Input Low Voltage	V_{IL}	-0.5	-	0.8	V
Operating Temperature	T_A	0	-	70	°C
	T_{AI}	-40	-	85	°C (8512I)

DC Electrical Characteristics (V_{CC}=5V±10%,T_A= -40°C to +85°C)

Parameter	*Symbol*	*Test Condition*	*min*	*max*	*Unit*
Input Leakage Current	I_{LI1}	$0V \le V_{IN} \le V_{CC}$	-8	8	µA
(A18, $\overline{CS}$)	I_{LI2}	$0.5V \le V_{IN} \le 2.7V$	-5	5	µA
Output Leakage Current	I_{LO}	$\overline{CS}=V_{IH}$, $V_{I/O}$=GND to V_{CC}	-4	4	µA
Operating Supply Current	I_{CC}	$\overline{CS}=V_{IL}$, $I_{I/O}$=0mA, minimum cycle	-	365	mA
Standby SupplyCurrent	I_{SB}	$\overline{CS}=V_{IH}$, minimum cycle	-	162	mA
	I_{SB1}	$\overline{CS} \ge V_{CC}$-0.2V, $0.2V \ge V_{IN} \ge V_{CC}$-0.2V	-	9.5	mA
-L Part	I_{SB2}	$\overline{CS} \ge V_{CC}$-0.2V, $0.2V \ge V_{IN} \ge V_{CC}$-0.2V	-	1.9	mA
Output Voltage	V_{OL}	I_{OL}=8.0mA	-	0.4	V
	V_{OH}	I_{OH}=-4.0mA	2.4	-	V

Typical values are at V_{CC}=5.0V,T_A=25°C and specified loading.

Capacitance (V_{CC}=5V±10%,T_A=25°C)

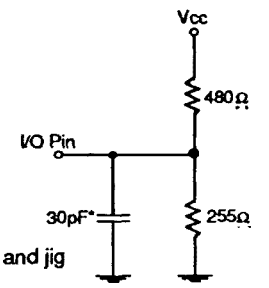
Parameter	*Symbol*	*Test Condition*	*max*	*Unit*
Input Capacitance ($\overline{CS}$, A18)	C_{IN1}	V_{IN} = 0V	15	pF
I/P Capacitance (other)	C_{IN2}	V_{IN} = 0V	20	pF
I/O Capacitance	$C_{I/O}$	$V_{I/O}$ = 0V	20	pF

Note: Capacitance calculated, not measured.

AC Test Conditions

* Input pulse levels: GND to 3.0V
* Input rise and fall times: 4ns
* Input and Output timing reference levels: 1.5V
* Output load: See Load Diagram
* V_{cc}=5V±10%

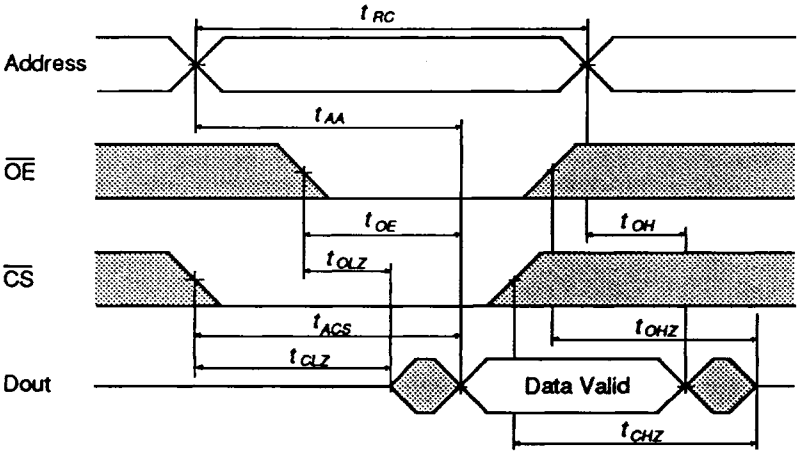
Output Load Circuit



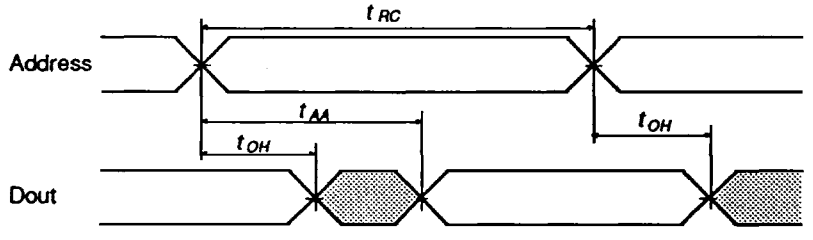
Read Cycle Timing

Parameter	Symbol	-25 min	-25 max	-30 min	-30 max	-35 min	-35 max	Unit	Note
Read Cycle Time	t_{RC}	25	-	30	-	35	-	ns	
Address Access Time	t_{AA}	-	25	-	30	-	35	ns	
Chip Select Access Time	t_{ACS}	-	25	-	30	-	35	ns	
Output Enable to Output Valid	t_{OE}	-	12	-	15	-	15	ns	
Output Hold from Address Change	t_{OH}	5	-	5	-	5	-	ns	
Chip Selection to Output in Low Z	t_{CLZ}	5	-	5	-	5	-	ns	1
Output Enable to Output in Low Z	t_{OLZ}	0	-	0	-	0	-	ns	1
Chip Deselection to Output in High Z	t_{CHZ}	0	12	0	15	-	15	ns	1
Output Disable to Output in High Z	t_{OHZ}	0	10	0	12	0	15	ns	1

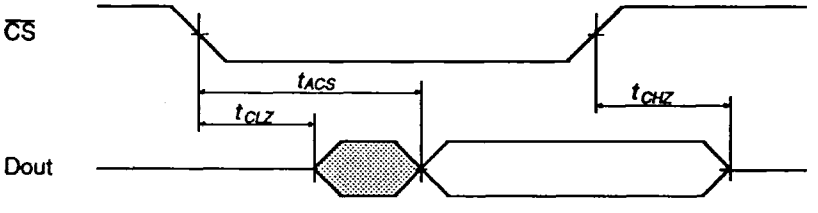
Read Cycle No.1 Timing Waveform (1,2)



Read Cycle No.2 Timing Waveform (1,2,3,5)



Read Cycle No. 3 Timing Waveform (1,2,4,5)



Notes:

1. Transition is measured ±200mV from steady voltage with Load B. This parameter is sampled and not 100% tested.
2. $\overline{WE}$ is High for Read Cycle.
3. Device is continuously selected, $\overline{CS}=V_{IL}$.
4. Address valid prior to or coincident with $\overline{CS}$ transition Low.
5. $\overline{OE}=V_{IL}$.

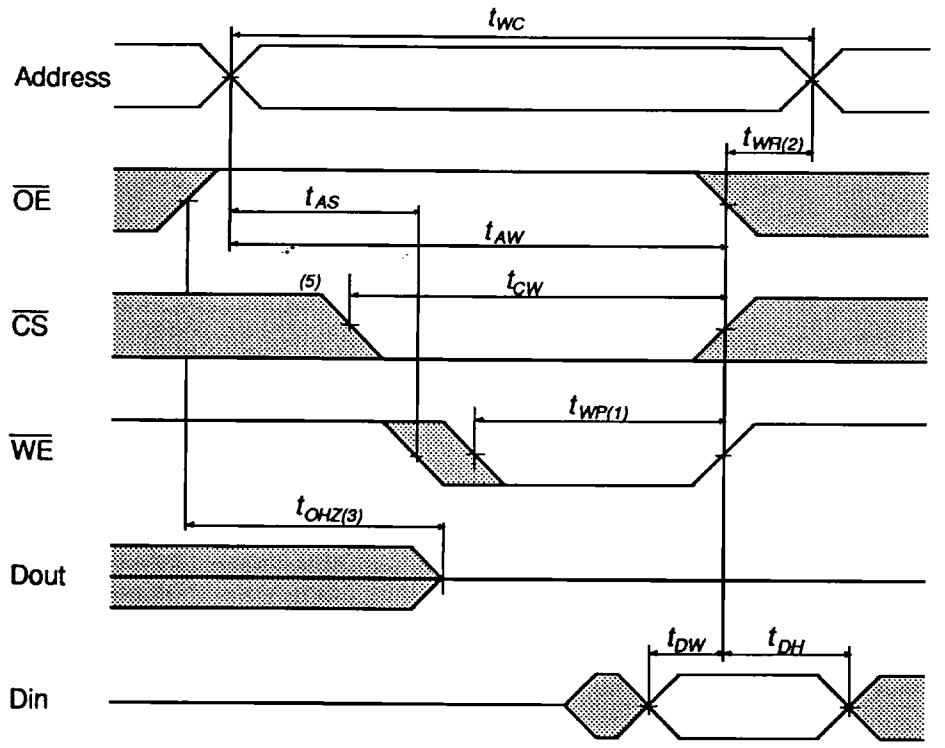
Write Cycle

Parameter	Symbol	-25 min	-25 max	-30 min	-30 max	-35 min	-35 max	Unit	Note
Write Cycle Time	t_{RC}	25	-	30	-	35	-	ns	
Chip Selection to End of Write	t_{CW}	20	-	25	-	30	-	ns	
Address Valid to End of Write	t_{AW}	20	-	25	-	30	-	ns	
Address Setup Time	t_{AS}	0	-	0	-	0	-	ns	
Write Pulse Width	t_{WP}	20	-	25	-	30	-	ns	
Write Recovery Time	t_{WR}	3	-	3	-	3	-	ns	
Write to Output in High Z	t_{WHZ}	0	15	0	18	0	20	ns	2
Data to Write Time Overlap	t_{DW}	15	-	18	-	20	-	ns	
Data Hold from Write Time	t_{DH}	0	-	0	-	0	-	ns	
Output Disable to Output in High Z	t_{OHZ}	0	10	0	13	0	15	ns	2
Output Active from End of Write	t_{OW}	0	-	0	-	0	-	ns	1

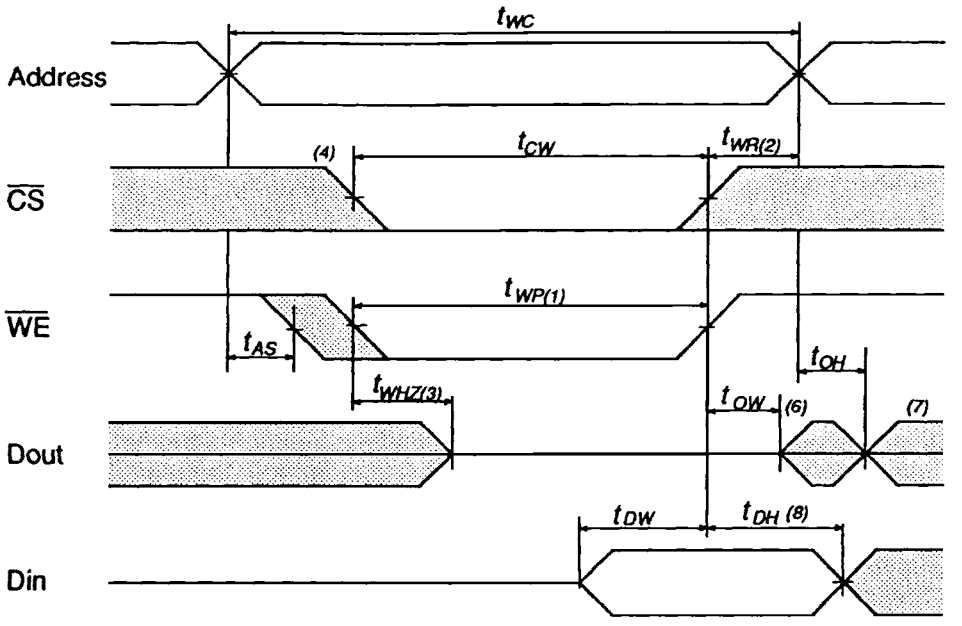
Notes:

1. Transition is measured ±200 mV from steady state voltage. This parameter is sampled and not 100% tested.
2. t_{WHZ} and t_{OHZ} are defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels.`These parameters are sampled and not 100% tested.

Write Cycle Timing Waveform



Write Cycle No.2 Timing Waveform (5)



Notes:

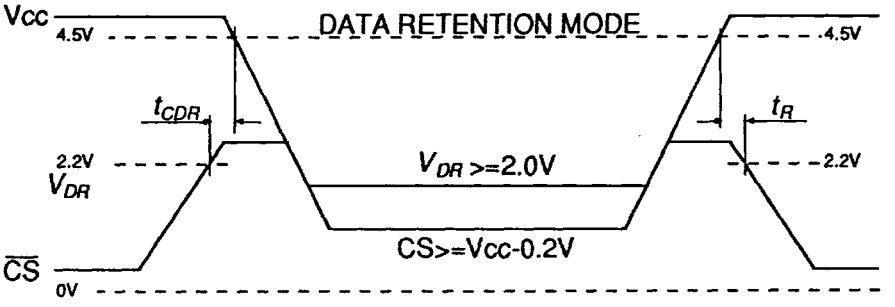
1. A write occurs during the overlap (t_{WP}) of a low $\overline{CS}$ and a low $\overline{WE}$.
2. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high to the end of write cycle.
3. During this period, I/O pins are in the output state. Input signals out of phase must not be applied.
4. If the $\overline{CS}$ low transition occurs simultaneously with or after the $\overline{WE}$ low transition, O/P's remain in a high impedance state.
5. $\overline{OE}$ is continuously low. ($\overline{OE}$=V_{IL})
6. Dout is in the same phase as written data of this write cycle.
7. Dout is the read data of next address.
8. If $\overline{CS}$ is low during this period, I/O pins are in the output state. I/P signals out of phase must not be applied to I/O pins.

Low V_{cc} Data Retention Characteristics - L Version Only (T_A= 0 to 70°C)

Parameter	*Symbol*	*Test Condition*	*min*	*max*	*Unit*
V_{CC} for Data Retention	V_{DR}	$\overline{CS}$>=V_{CC}-0.2V	2.0	-	V
Data Retention Current	I_{CCDR}	V_{CC}=3.0V, $\overline{CS}$≥V_{CC}-0.2	-	450	µA
Chip Deselect to Data Retention Time	t_{CDR}	See Retention Waveform	0	-	ns
Operation Recovery Time	t_R	See Retention Waveform	t_{RC} (1)	-	ns

Notes: (1) t_{RC}=Read Cycle Time

Low V_{cc} Data Retention Timing Waveform - L Version Only



Ordering Information

MS8512FKL-25

Speed	25	= 25ns
	30	= 30 ns
	35	= 35 ns
Temp. range/screening	Blank	= Commercial Temp.
Power Consumption	Blank	= Standard Part
	L	= Low Power Part
Package	FK	= Plastic 32 pin DIP
Organization	8512	= 512K x 8

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